**Abstract**

Transparent thin films of pure and Ga doped CuO thin films were deposited on the glass plates at 450°C by spray pyrolysis technique. The various volumes of Ga precursor solution from 0.5, 1.0, 1.5 and 2.0 mlwere mixed with CuO precursor solution. The deposited films were characterized by X-ray diffraction (XRD), scanning electron microscope (SEM) and optical studies. X-ray diffraction patterns of pure and Ga doped CuO thin films reveal the polycrystalline nature and cubic structure. The surface morphology of the film is found to be influenced with the Ga doping. Optical transmittance and absorption studies were also recorded in the wavelength range 300 nm to 1100 nm. The band gap of the film is found to be decrease from 2.79eV to 2.24eV.